

APPLICATION DATA SHEET

Electronic Version v14

Stylesheet Version v14.0

Title of Invention	STRUCTURE AND METHOD OF FORMING BIPOLAR TRANSISTOR HAVING A SELF-ALIGNED RAISED EXTRINSIC BASE USING SELF-ALIGNED ETCH STOP LAYER
Application Type :	regular, utility
Attorney Docket Number :	FIS920030412US1
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Customer Number:	32074
	
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